

Notification about the transfer of the semiconductor business

The semiconductor business of Panasonic Corporation was transferred on September 1, 2020 to Nuvoton Technology Corporation (hereinafter referred to as "Nuvoton"). Accordingly, Panasonic Semiconductor Solutions Co., Ltd. became under the umbrella of the Nuvoton Group, with the new name of Nuvoton Technology Corporation Japan (hereinafter referred to as "NTCJ").

In accordance with this transfer, semiconductor products will be handled as NTCJ-made products after September 1, 2020. However, such products will be continuously sold through Panasonic Corporation.

Publisher of this Document is NTCJ.

If you would find description "Panasonic" or "Panasonic semiconductor solutions", please replace it with NTCJ.

※ Except below description page

"Request for your special attention and precautions in using the technical information and semiconductors described in this book"

Nuvoton Technology Corporation Japan

MTM78E2B0LBF

Gate Resistor installed Dual N-Channel MOS Type

For lithium-ion secondary battery protection circuit

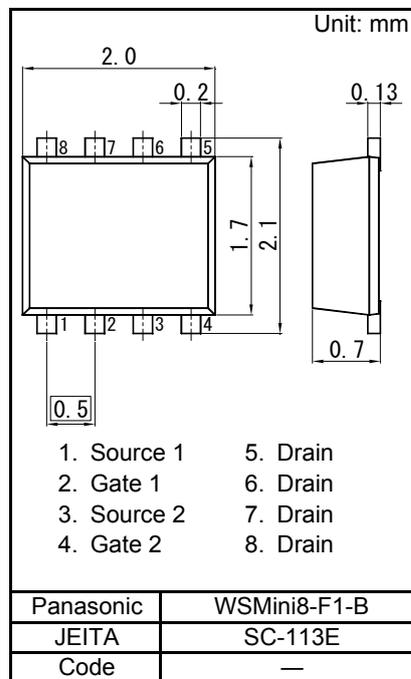
■ Features

- Low drain-source On-state Resistance
 $R_{DS(on)}$ typ. = 21.5 m Ω (VGS = 4.0 V)
- Halogen-free / RoHS compliant
 (EU RoHS / UL-94 V-0 / MSL:Level 1 compliant)

■ Marking Symbol: 5A

■ Packaging

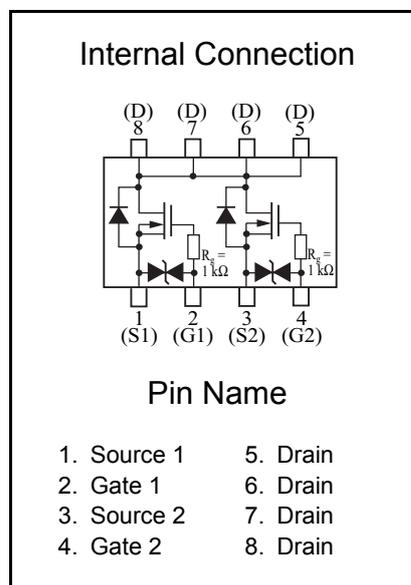
Embossed type (Thermo-compression sealing) : 3 000 pcs / reel (standard)



■ Absolute Maximum Ratings Ta = 25 °C

Parameter		Symbol	Rating	Unit
FET1	Drain-source Voltage	VDS	20	V
	Gate-source Voltage	VGS	±12	V
FET2	Drain current	ID	4.0	A
	Peak drain current *1	IDp	40	A
Overall	Total power dissipation	PD1 ²	700	mW
		PD2 ³	150	
Overall	Channel temperature	Tch	150	°C
	Operating ambient temperature	Topr	-40 to +85	°C
	Storage temperature	Tstg	-55 to +150	°C

- Note) *1 t = 10 μ s, Duty Cycle < 1 %
 Ceramic substrate (70 × 70 × t 1.0 mm)
 *2 Dual operating
 *3 Stand-alone (without the substrate)



■ Electrical Characteristics Ta = 25°C ± 3°C

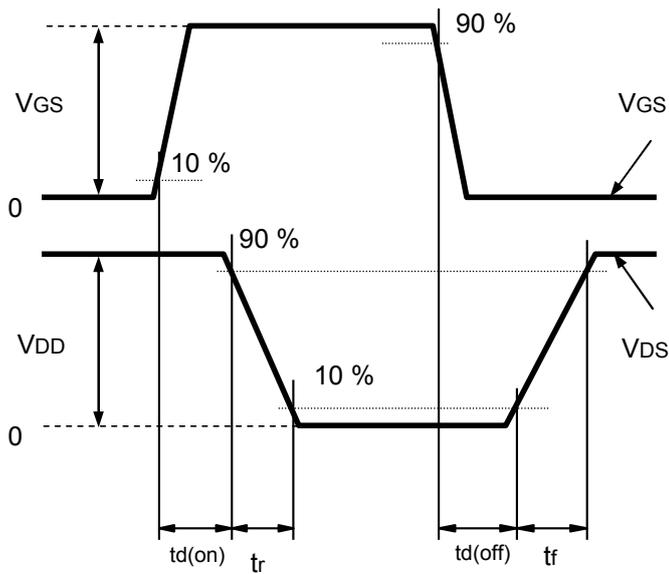
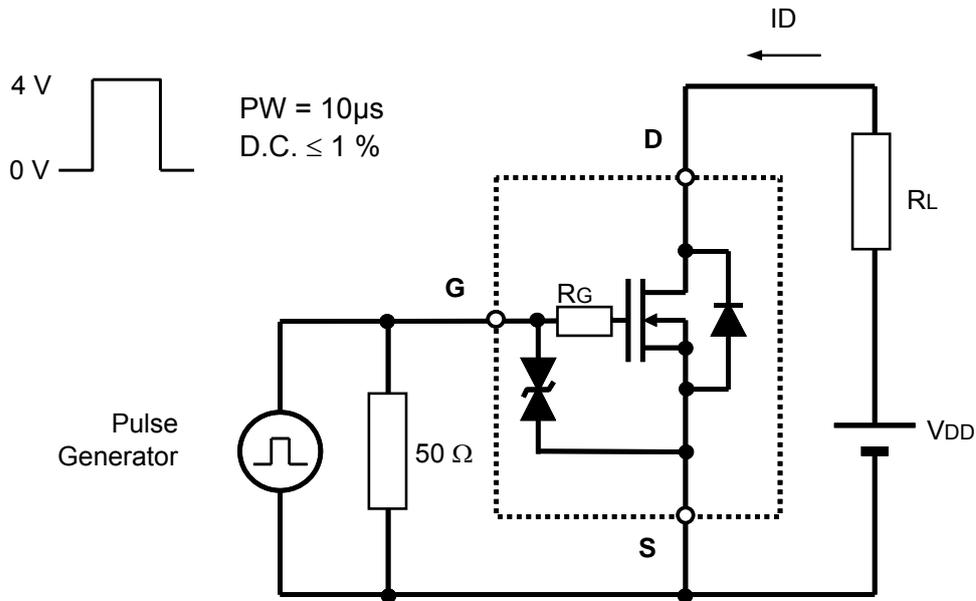
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Drain-source surrender voltage	VDSS	ID = 1.0 mA, VGS = 0	20			V
Drain-source cutoff current	IDSS	VDS = 20 V, VGS = 0			1.0	μA
Gate-source cutoff current	IGSS	VGS = ±12 V, VDS = 0			±10	μA
Gate threshold voltage	Vth	ID = 1.0 mA, VDS = 10 V	0.40	0.85	1.30	V
Drain-source ON resistance	RDS(ON)1	ID = 2.0 A, VGS = 4.0 V		21.5	25.0	mΩ
	RDS(ON)2	ID = 1.5 A, VGS = 3.0 V		26.0	30.0	mΩ
	RDS(ON)3	ID = 1.0 A, VGS = 2.5 V		30.0	36.0	mΩ
Forward transfer admittance	Yfs	ID = 1.0 A, VDS = 10 V	1.0			S
Short-circuit input capacitance (Common source)	Ciss	VDS = 10 V, VGS = 0, f = 1 MHz		1100		pF
Short-circuit output capacitance (Common source)	Coss			75		pF
Reverse transfer capacitance (Common source)	Crss			70		pF
Turn-on delay time ^{*1, *2}	td(on)				0.2	
Rise time ^{*1, *2}	tr	VDD = 10 V, VGS = 4 V,				
Turn-off delay time ^{*1, *2}	td(off)	ID = 1.0 A, RL = 10 Ω				
Fall time ^{*1, *2}	tf					
				1.5		μs

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

2. *1 t = 10 μs, Duty Cycle < 1 %

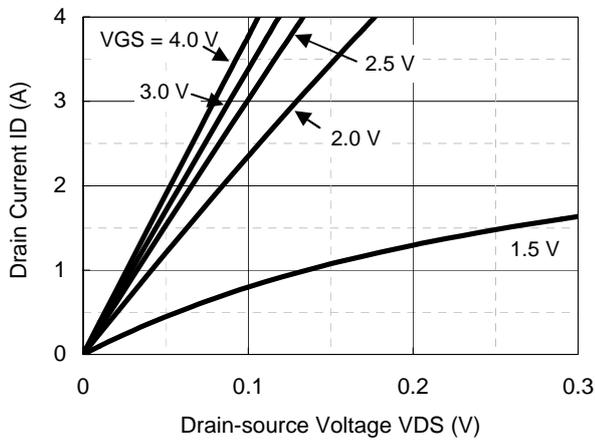
*2 Measurement circuit for Turn-on Delay Time/Rise Time/Turn-off Delay Time/Fall Time

*2 Measurement circuit for Turn-on Delay Time/Rise Time/Turn-off Delay Time/Fall Time

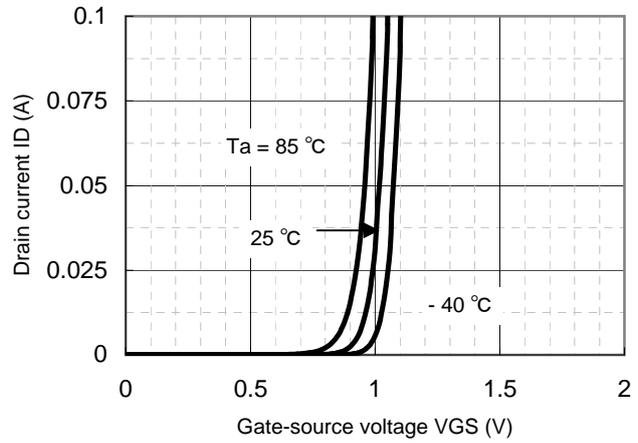


Technical Data (reference)

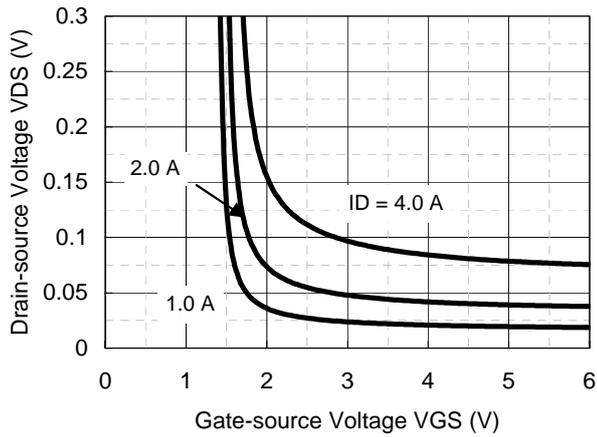
ID - VDS



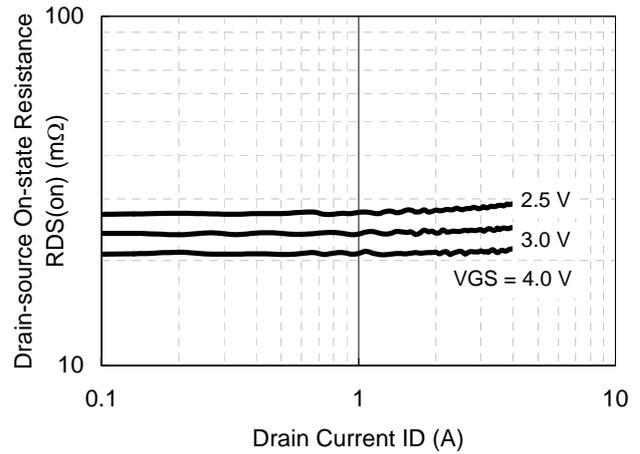
ID - VGS



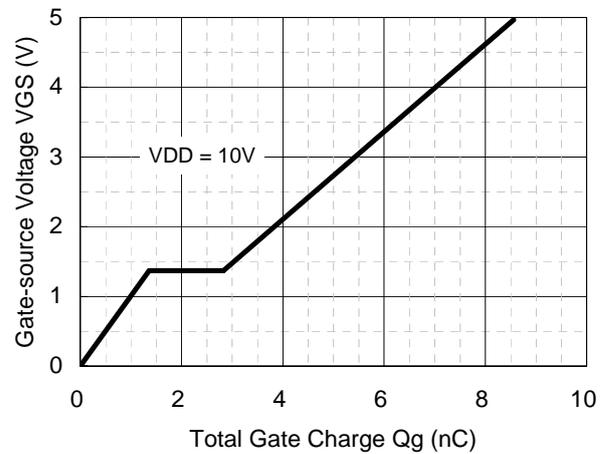
VDS - VGS



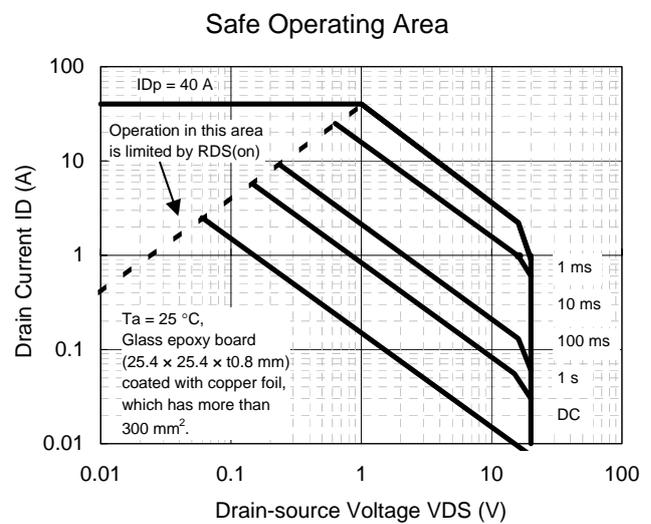
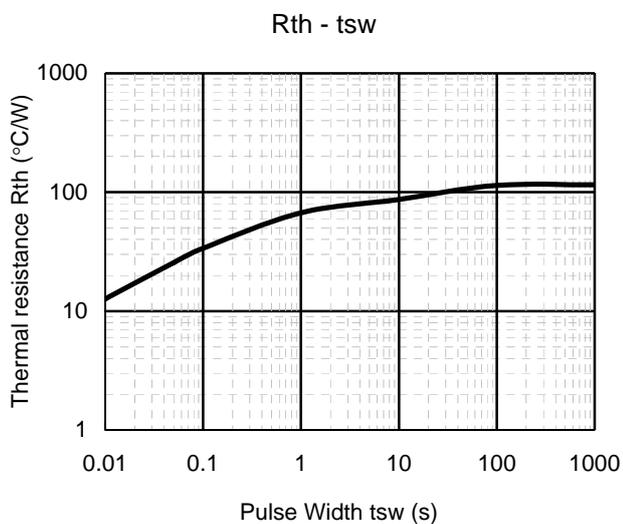
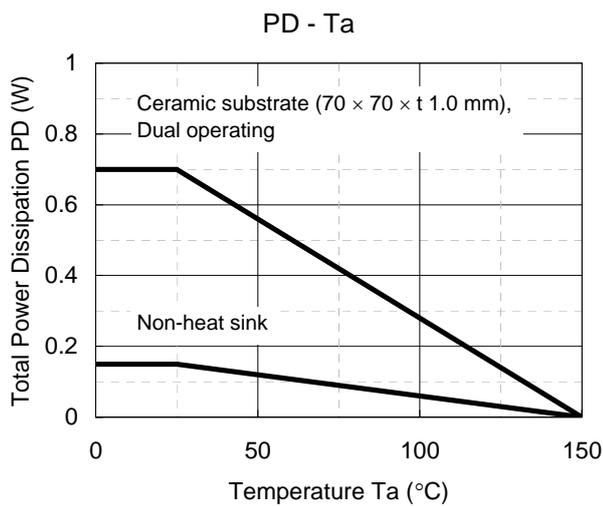
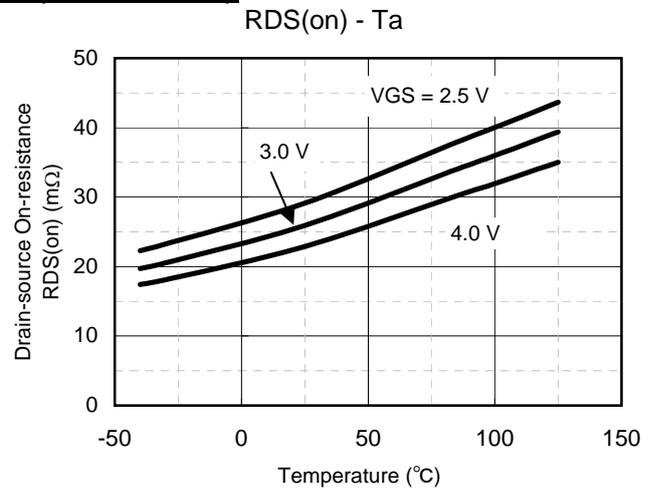
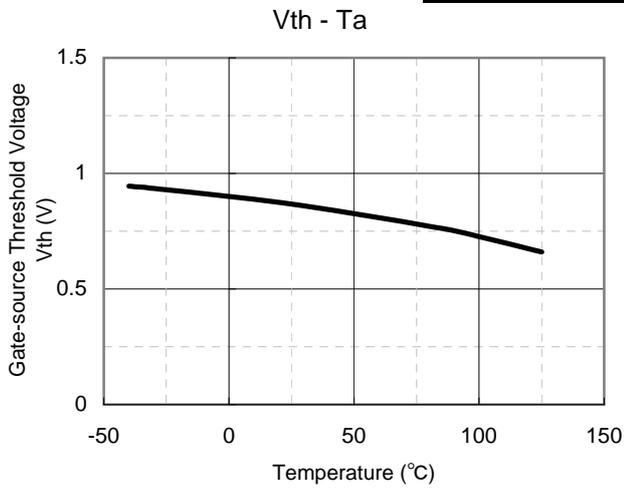
RDS(on) - ID



Dynamic Input/Output Characteristics

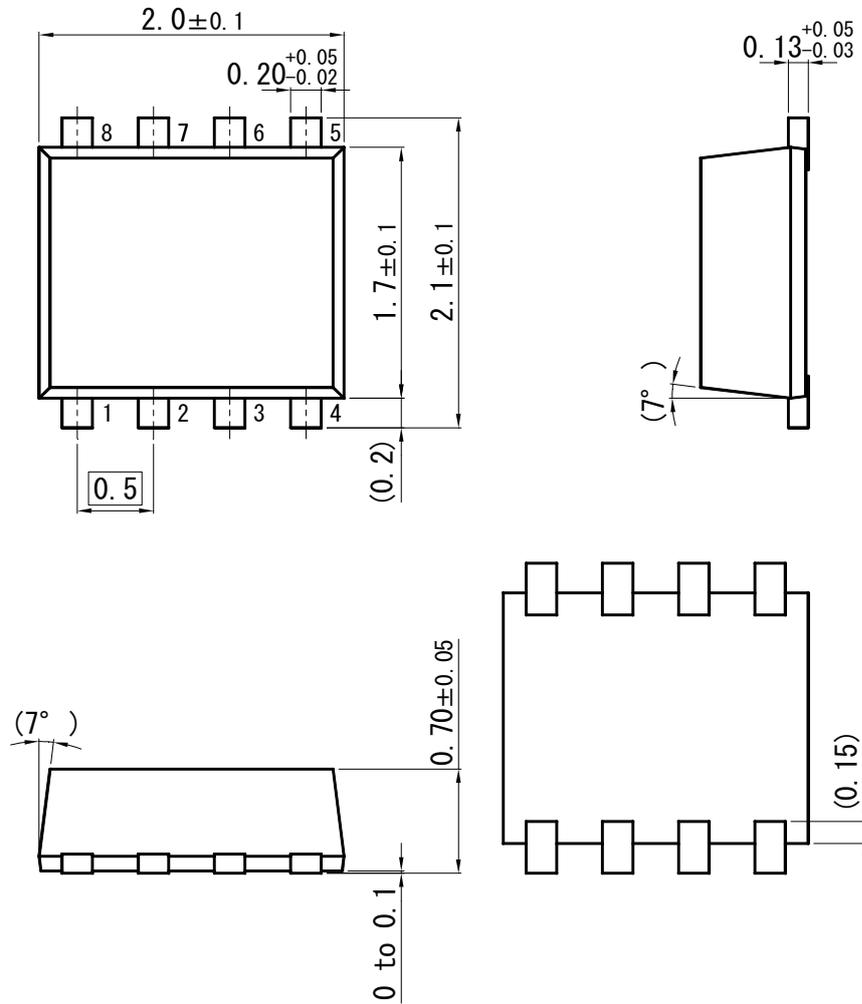


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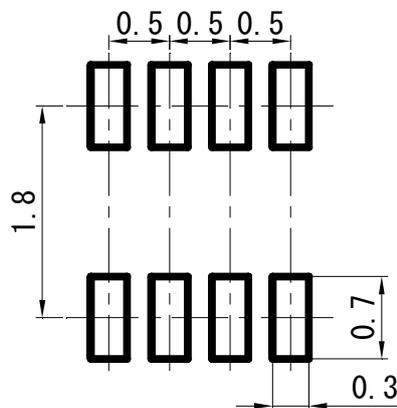


WSMini8-F1-B

Unit : mm



■ Land Pattern (Reference) (Unit : mm)



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